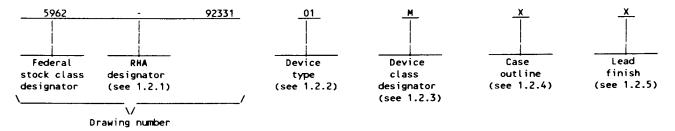
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5962-E462-93

<u>DISTRIBUTION STATEMENT A.</u> Approved for public release; distribution is unlimited.

#### 1. SCOPE

- 1.1 <u>Scope</u>. This drawing forms a part of a one part one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes Q and M) and space application (device class V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
  - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 <u>RHA designator</u>. Device class M RHA marked devices shall meet the MIL-1-38535 appendix A specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-1-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
  - 1.2.2 Device type(s). The device type(s) shall identify the circuit function as follows:

Device type	<u>Generic number</u>	<u>Circuit function</u>				
01	TMC2330V	CMOS Coordinate Transformer, 16 x 16 Bit, 55 ns				
02	TMC2330V1	CMOS Coordinate Transformer, 16 x 16 Bit, 45 ns				

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class

Device requirements documentation

M

Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883

Q or \

Certification and qualification to MIL-I-38535

1.2.4 Case outline(s). The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
x	CMGA5-P120	120	Pin grid array
Y	CQCC1-G132	132	Gullwing leaded chip carrier

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for class M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

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DESC FORM 193A

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# 1.3 Absolute maximum ratings. 1/ Supply Voltage range . . . . . . . . . . . . . . -0.5V dc TO 7.0V dc Output short circuit duration $4/\ldots$ 1 second Power dissipation, unloaded (PD) . . . . . . . . . 975 mW Junction temperature $(T_j)$ . . Thermal resistance, junction-to-case $(\theta_{\text{JC}})$ . . . . See MIL-STD-1835 1.4 <u>Recommended operating conditions</u>. Supply voltage range (V<sub>DD</sub>) . . . . . . . . . . 4.5V dc to 5.5V dc Input LOW voltage (V<sub>IL</sub>) ... ... ... ... ... 8V dc maximum Input HIGH voltage (V<sub>IH</sub>) ... ... ... 2.0V dc minimum Input LOW current (I<sub>OL</sub>) ... ... ... 8 mA maximum Input HIGH current (IOH) . . . . . . . . . . . . -4 mA minimum Clock pulse width, LOW (TpWL) Clock pulse width, HIGH (TpwH) Device type 01 . . . . . . . . . . . . . 8 ns minimum Device type 02 . . . . . . . . . . . . . . 6 ns minimum Data Input setup time (ts) Case operating temperature range ( $T_C$ ) . . . . . . -55°C to +125°C 1.5 <u>Digital logic testing for device classes Q and V.</u> Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012) . . . . . . XX percent $\frac{5}{2}$ Absolute maximum ratings are limiting values applied individually while all other parameters are within specified operating conditions. Functional operation under any of these conditions is NOT applied. Applied voltage must be current limited to specified range, and measured with respect to GND. Forcing voltage must be limited to specified range. <u>3</u>/ 4/ Single output in HIGH state to GND. Values will be added when they become available.

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### 2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards bulletin, and handbook</u>. Unless otherwise specified, the following specification, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-I-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

MIL-STD-973 - Configuration Management.
MIL-STD-1835 - Microcircuit Case Outlines.

BULLETIN

MILITARY

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

HANDBOCK

MILITARY

MIL-HDBK-780 - Standardized Military Drawings.

(Copies of the specification, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

#### 3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V and herein.
  - 3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.
  - 3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.
  - 3.2.3 Logic diagram. The logic diagram shall be as specified on figure 2.
  - 3.2.4 Block diagram. The block diagram shall be as specified on figure 3.
  - 3.2.5 Radiation exposure circuit. The radiation exposure circuit shall be as specified when available.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.

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- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.
- 3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-I-38535.
- 3.6 <u>Certificate of compliance</u>. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M, the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-1-38535 and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M</u>. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M</u>. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 105 (see MIL-1-38535, appendix A).
  - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturer's QM plan.

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Test	Symbol	Conditions $\underline{1}/$ $-55^{\circ}C \leq T_{C} \leq +125^{\circ}C$	Group A subgroups	Device type	Limits		Unit
		$4.5 \text{ V} \leq \text{V}_{DD}^{\text{U}} \leq 5.5 \text{ V}$ unless otherwise specified			Min	Max	1
Quiescent supply current	IDDQ	v <sub>DD</sub> = 5.5 v, v <sub>in</sub> = 0v	1,2,3	ALL		10	m#
Dynamic supply current, unloaded	IDDU	$V_{DD} = 5.5 \text{ V}, f = 20 \text{ MHz}$ $\overline{\text{OERX}}, \overline{\text{OEPY}} = V_{DD}$	1,2,3	ALL		175	m/
Input LOW current	IIL	V <sub>DD</sub> = 5.5 v, v <sub>in</sub> = 0v	1,2,3	ALL	-10	10	Щ
Input HIGH current	IIH	v <sub>DD</sub> = 5.5 v, v <sub>in</sub> = v <sub>DD</sub>	1,2,3	ALL	-10	10	Щ
Output LOW voltage	V <sub>OL</sub>	V <sub>DD</sub> = 4.5 V, IOL = 8 mA	1,2,3	ALL		0.4	v
Output HIGH voltage	v <sub>он</sub>	V <sub>DD</sub> = 4.5 V, IOH = -4 mA	1,2,3	ALL	2.4		v
Output leakage current, output LOW	<sup>I</sup> ozt	v <sub>DD</sub> = 5.5 v, v <sub>in</sub> = 0v	1,2,3	ALL	-40	40	l l
Output leakage current, output HIGH	I <sub>OZH</sub>	v <sub>DD</sub> = 5.5 v, v <sub>in</sub> = v <sub>DD</sub>	1,2,3	ALL	-40	40	Щ
Short circuit <u>2</u> / output current	<sup>1</sup> os	V <sub>DD</sub> = 5.5 V, output HIGH one pin to GND, one second duration max	1,2,3	ALL	-20	100	m/
Input capacitance	CIN	T <sub>A</sub> = 25°C, f = 1 MHz see 4.4.1c	4	ALL		15	pf
Output capacitance	Cout	T <sub>A</sub> = 25°C, f = 1 MHz	4	ALL		15	p

See footnotes at the end of the table.

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TABLE I. <u>Electrical performance characteristics</u>. (continued)

Test	Symbol	Conditions 1/ $-55^{\circ}C \le T_{C} \le +125^{\circ}C$	Group A subgroups	Device type	Limits		Unit
		$4.5 \text{ V} \leq \text{V}_{DD}^{\text{T}} \leq 5.5 \text{ V}$ unless otherwise specified			Min	   Max	
Functional testing 3/		V <sub>DD</sub> = 5 V, see 4.4.1b	7,8A,8B	ALL		   	
Digital output delay 3/4/	t <sub>D</sub>	V <sub>DD</sub> = 4.5 V	9,10,11	01		25	ns
=, <u>=</u> , <u>-</u> ,		see Figure 4	10	02		23	n:
Digital output hold time <u>3</u> /	t <sub>HO</sub>	V <sub>DD</sub> = 5.5 V see Figure 4	9,10,11	ALL		4	ns
Output enable delay 4/	<sup>t</sup> ena	V <sub>DD</sub> = 4.5 V	9,10,11	01		17	ns
<b>,</b>		see Figure 4	10	02		16	ns
Output disable delay 4/	t <sub>DIS</sub>	V <sub>DD</sub> = 4.5 V	9,10,11	01		17	ns
, <u>-</u>		see Figure 4	10	02		16	n
		·	+				+

<sup>1/</sup> All testing to be performed using worst-case test conditions unless otherwise specified.

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 $<sup>\</sup>underline{2}$ / Not more than one output should be shorted.

 $<sup>\</sup>underline{3}$ / All transitions are measured at 1.5 V level.

<sup>4/</sup> Device 02 is differentiated from device 01 at +125°C only, (following 25°C and -55°C testing).

DEVICE TYPES 01 AND 02

×	
OUTLINE	
CASE	

A2 .	ZAME	z	NAME	PIN	NAME	N d	NAME	NId	NAME	N N	NAME	PIN	NAME	ğ	NAME
A2 F	PYOUT 5	8	PYOUT 6	cs	GND	ū	RTP	5	GND		YPIN 2	110	YPIN	M12	XR!N
	YOUT	40	PYPUT 9	9	00,	E2	QND	G12	XRIN 12		YPIN 4	-	יל מפא	X	XRIN
₹	YOUT	82	PYOUT 11	72	GND	ü	QQA	613	XRIN 13		ONS	112	XRIN.	z	YPINA
A.	YOUT 10	98	PYOUT 13	ස	00/	<u></u>	200	Ξ	ACCO		ONS	113	XRIN	N2	YPIN
-	YOUT 12	87	OVF.	<u>හ</u>	QNS	£12	CND	H2	ACC 1		XRIN	Ē	YPIN	Ź	YPIN
	YOUT 14	88	RXOUT 1	010	QNG	£13	OERX	Î	. 00/	K13	XRIN	M2	YPIN 0	Ž	YPIN 15
	YOUT 15	68	RXOUT 3	5	App.	Ē	TCXY	Ξ	XRIN 9		YPIN	3	YPIN	SN SN	YPIN 17
	2XOUT	B10	RXOUT 5	C12	RXOUT 11	F2	QND	H12	XRIN 10	77	YPIN 3	¥	YPIN	92	YPIN
	3XOUT 2	811	RXOUT 7	C13	RXOUT 13	ũ	CK CK	H13	XRIN	n	CNO	¥	YPIN 1	ž	YPIN 21
	XXOUT 4	B12	RXOUT 9	5	OEPY	==	00^	5	VPIN 0	<u></u>	\ \ \ \	9	YPIN	8 N	YPIN 55
_	XOUT	813	RXOUT 12	02	PYOUTO	F12	XRIN 15	75	YPIN 1	2	Y PIN	Ē	YPIN	6 Z	YPIN 24
	SXOUT R	5	PYOUT 1	03	CND	F13	XRIN 14	13	YPIN	9	* 'C' >	<b>8</b>	YPIN 23	Š	YPIN 26
	XOUT 10	C5	PYOUT 2	10	QNS	5	ENYP	=======================================	CNO	7	ON S	£	YPIN 25	Z	YPIN 29
	YOUT	C	7 00 /	012	RXOUT 14	C2	ENYP <sub>0</sub>	712	XRIN 7	83	۷٥٥	<u>¥</u>	YPIN 53	N12	YPIN 30
В2 Р	YOUT 4	ಶ	GND	513	RXOUT 15	S	OND	J13	XRIN 8	6	YPIN 27	Ξ	ENXR	N13	XRINO

<b>&gt;</b> -
T.INE
Ö
CASE

					כיסר כסובוייר						
ğ	NAME	PIN	NAME	N N	NAME	<u>a</u>	NAME	N.	NAME	P.IN	NAME
							-				
_	00 /	23	YPIN 1	45		67	00,	68	GND	=	RXOUT
7	S Z	24	YPIN 2	46	YPINIA	68	XRIN.	06	RXOUT, 5	112	, 000
'n	PYOUT 4	25	YPIN 3	47	YPIN	69	XRIN,	9	, og/	113	RXOUT,
+	PYOUT 1	56	VPIN ₹	48	YPIN	70	CONS	92	RXOUT,	114	RXOUT
2	OND	27	YPIN 5	49	CND CND	71	XRIN	93	RXOUT	115	OVF
9	PYOUT 2	28	YPIN 6	20	YPIN 21	72	S S	46	RXOUT	116	QNS
7	PYOUT ?	59	ONS	51	YPIN 22	73	XRIN	95	CND	117	PYOUT, 5
<b>6</b> 0	PYOUT 0	ကို	YPIN 7	52	YPIN	74	XRINS	96	RXOUT.	118	PYOUT:
on.	00^	31	YPIN	53	2,000	75	ONS	97	RXOUT	119	PYOUT
0	OEP?	32	N S	54	YPIN	16	XRING	86	NC C	120	, oo
=	QNS	33	QNS	55	YPIN25	77	XRIN7	66	200	121	PYOUT.,
12	RTP	34	Y N O	99	YPIN	78	XRINA	100	RXOUT	•	PYOUT !
13	ر لا	35	S S	57	YPIN	79	XRING	101	NC O	-	PYOUT
<b>±</b>	CNS	36	YPIN 10	58	YPIN	80	XRIN	102	RXOUTA	124	OND OND
15	TCXY	37	2 00	59	YPIN	8	XRIN	103	N S	-	PYOUT
16	ENYPO	38	YPIN 11	9	VPIN 30	82	XRIN12	104	QNS	_	PYOUT
17	GND	39	YPIN 12	6	YPIN	83	l QNS	105	RXOUT-	-	PYOUT,
80	ENTP	9	YPIN	62	S S	84	XRIN11	106	RXOUT,	-	NC ,
6	ACC	4	YPIN 14	63	ENXR	85	XRINIA	107	RXOUT	-	QNS
50	ACC 1	42	YPIN 15	64	NC NC	96	XRIN	108	o O O O O O O	_	PYOUT
51	00,	3	YPIN 16	65	Ş	87	00	109	RXOUT.	_	N N
22	VPIN 0	\$	71 NIGA	99	XRINO	88	OERX	110	RXOUT3	132	PYOUTS

FIGURE 1. <u>Terminal connections</u>.

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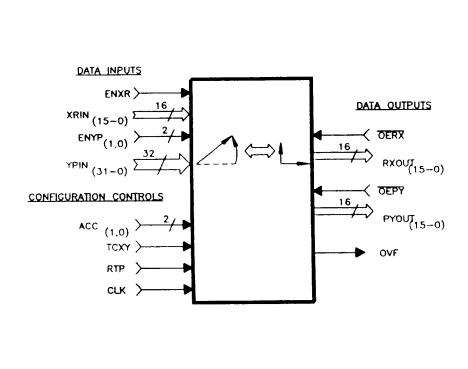
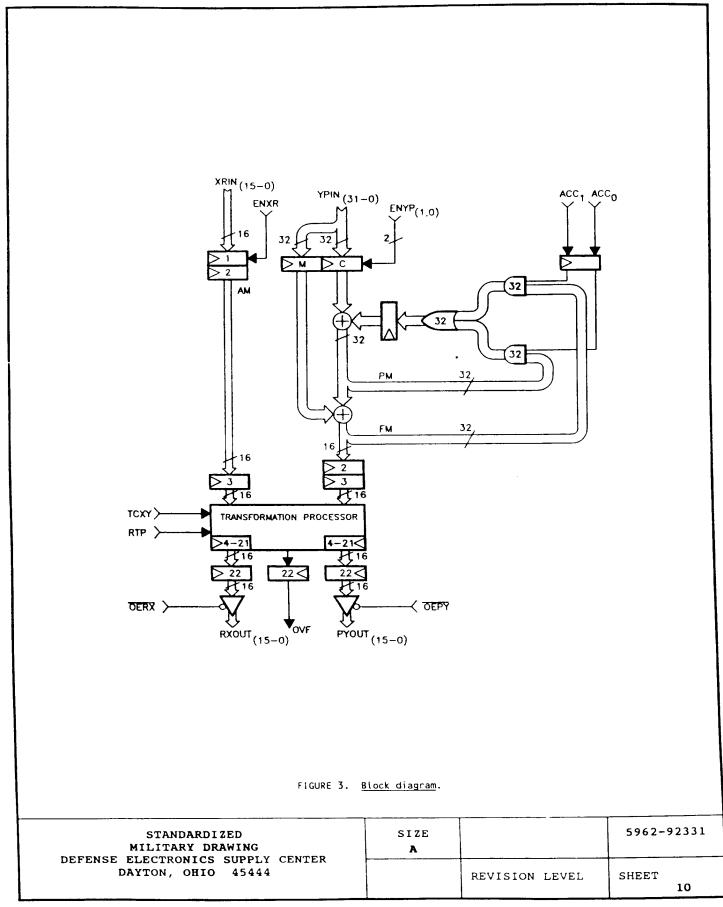
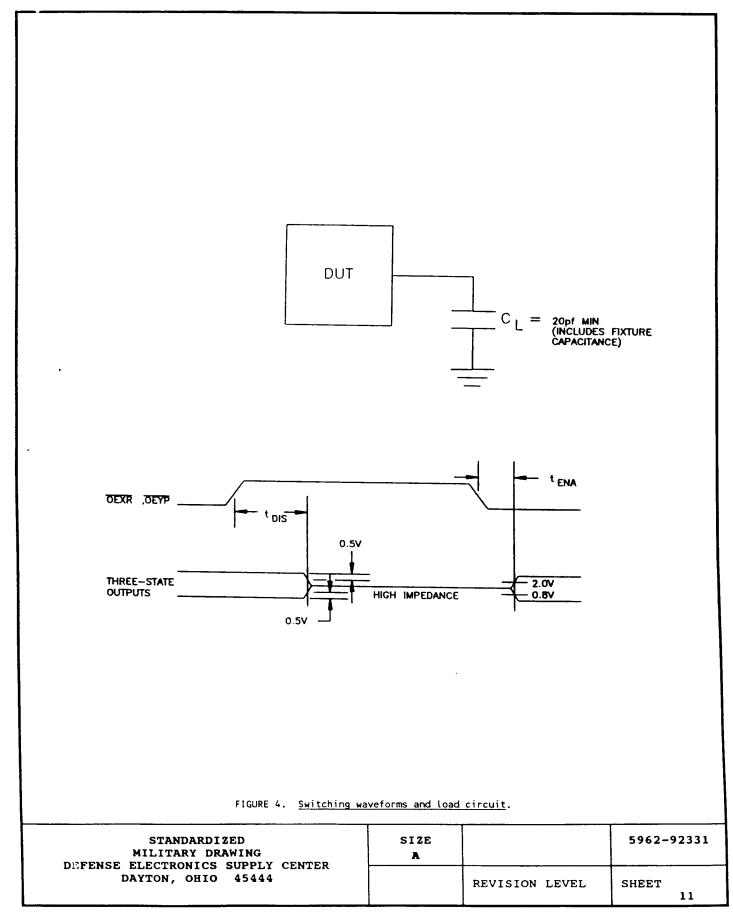
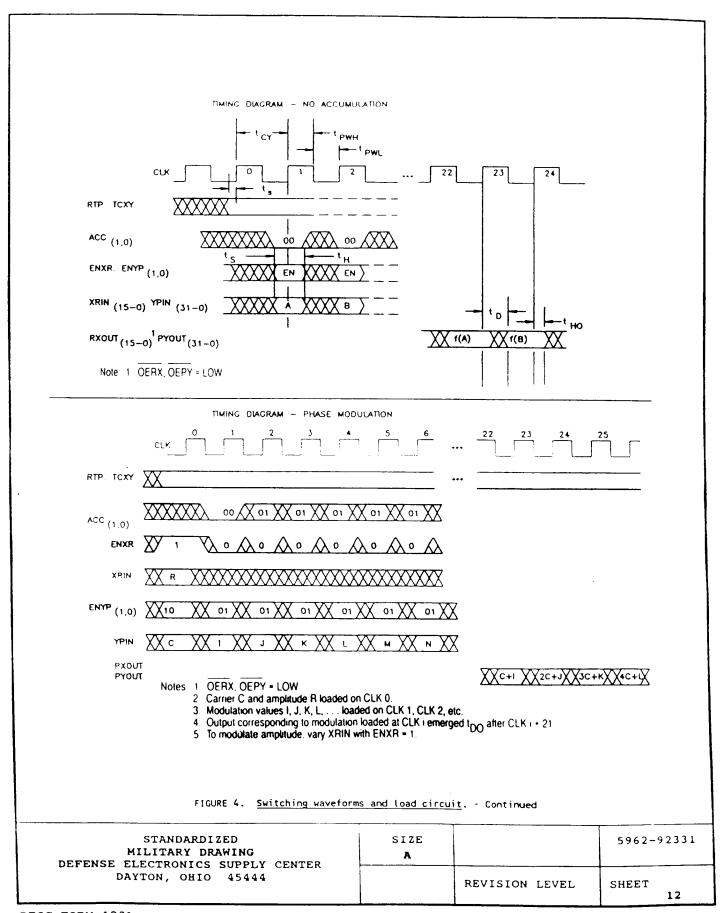


FIGURE 2. Logic diagram.

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- 4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.
  - 4.2.1 Additional criteria for device class M.
    - a. Burn-in test, method 1015 of MIL-STD-883.
      - (1) Test condition A or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
      - (2)  $T_A = +125$ °C, minimum.
  - b. Interim and final electrical test parameters shall be as specified in table II herein.
  - 4.2.2 Additional criteria for device classes Q and V.
    - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
    - b. Interim and final electrical test parameters shall be as specified in table II herein.
    - Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.
- 4.3 <u>Qualification inspection for device classes Q and V.</u> Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.
  - 4.4.1 Group A inspection.
    - a. Tests shall be as specified in table II herein.
    - b. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
    - c. Subgroup 4(C<sub>IN</sub> and C<sub>OUT</sub> measurements) shall be measured only for the initial design and after process or design changes which may affect capacitance. A minimum sample size of 5 devices with zero rejects shall be required.
- 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

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- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
  - a. Test condition A or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
  - b.  $T_A = +125$ °C, minimum.
  - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

TABLE II. <u>Electrical test requirements</u>.

Test requirements	Subgroups (in accordance with MIL-STD-883, TM 5005, table 1)	Subgroups (in accordance MIL-I-38535, tak	with .
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)			1, 7, 9
Final electrical parameters (see 4.2)	1, 2, 3, 7, 8, <u>1</u> / 9, 10, 11	1, 2, 3, 7, <u>1</u> / 8, 9, 10, 11	1, 2, 3, 7, <u>2</u> / 8, 9, 10, 11
Group A test requirements (see 4.4)	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7 8, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 7, 9	1, 2, 7, 9	1, 2, 7, 9
Group D end-point electrical parameters (see 4.4)	1, 2, 7, 9	1, 2, 7, 9	1, 2, 7, 9
Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9	1, 7, 9

 $<sup>\</sup>frac{1}{2}$ / PDA applies to subgroup 1.

4.4.2.2 <u>Additional criteria for device classes Q and V</u>. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-1-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-1-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.

4.4.3 <u>Group D inspection</u>. The group D inspection end-point electrical parameters shall be as specified in table II herein.

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<sup>2/</sup> PDA applies to subgroups 1 and 7.

- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RMA levels for device classes Q and V shall be M, D, R, and H and for device class
  - a. End-point electrical parameters shall be as specified in table II herein.
  - b. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-I-38535, appendix A, for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-I-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T<sub>A</sub> = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.
  - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
  - 5. PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V.
  - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
  - 6.1.2 <u>Substitutability</u>. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444-5270, or telephone (513) 296-5377.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-I-38535, MIL-STD-1331 and Table III.

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	TA	BLE III. PIN F	ONCITONS.		
V <sub>DD</sub> , GND	The device operates from a singl	e +5V supply.	All power as	nd ground pins must be cor	nnected.
CLOCK					
CLK	The device operates from a singl which is the reference for all t			sters are strobed on the I	rising edge of CLK,
INPUTS/OUTPUT	S		<del></del>		
XRIN <sub>15-0</sub>	XRIN <sub>15-0</sub> is the registered Carte input data port. XRIN <sub>15-0</sub> is th	sian X-coordina e MSB.	ate or Polar	Magnitude (Radius) 16-bit	:
YPIN <sub>31-0</sub>	YPIN <sub>31-0</sub> is the registered Carte is the MSB.	sian Y-coordina	ate or Polar	Phase angle 32-bit input	data port. YPIN31
RXOUT <sub>15-0</sub>	RXOUT <sub>15-0</sub> is the registered Pola is the MSB.	r Magnitude (Ra	adius) or X-d	coordinate 16-bit output o	data port. RXCUT <sub>15</sub>
PYOUT 15-0	PYOUT <sub>15-0</sub> is the registered Pola PYOUT <sub>15</sub> is the MSB.	r Phase angle o	or Cartesian	Y-coordinate 16-bit outpu	ut data port.
CONTROLS					
	The value presented to the input when ENXR is HIGH. When ENXR is	port XRIN is l LOW, the value	latched into	the input registers on th the register remains uncha	ne current clock anged.
ENXR	The value presented to the input when ENXR is HIGH. When ENXR is  The value presented to the YPIN the current clock, as determined	input port is i	stored in t	the register remains uncha	anged.
ENXR	The value presented to the YPIN the current clock, as determined	input port is i	stored in t	the register remains uncha	anged.
ENXR	when ENXR is HIGH. When ENXR is  The value presented to the YPIN the current clock, as determined  ENYP1,0 INST  00 No in the current in the current in the current clock, as determined in the current clock, as	input port is to by the control	e stored in to latched into l inputs ENYF ed, current enabled, C da enabled, M da	the register remains unchared the phase accumulator in P1,0 as shown below:  data held ata held ata held	anged.
ENXR	when ENXR is HIGH. When ENXR is  The value presented to the YPIN the current clock, as determined  ENYP1,0 INST  00 No in the current in the current in the current clock, as determined in the current clock, as	input port is to by the control  TRUCTION  registers enable egister input energister set to bled	e stored in to latched into l inputs ENYA ed, current enabled, C de enabled, M de O, C registo	the register remains unchar the phase accumulator inp P1,0 as shown below:  data held ata held ata held ata input	out registers on
ENYP1,0	when ENXR is HIGH. When ENXR is  The value presented to the YPIN the current clock, as determined  ENYP1,0 INST  OO NOT 10 C received in the current of the	input port is less to be current transport output ports.	e stored in to latched into linputs ENYF ed, current enabled, C da enabled, M da O, C registe odulation re sformation m ion. When R	the phase accumulator ing P1,0 as shown below:  data held ata held ata held er input  gister, and 0=LOW, 1=HIGH node of the device. When	out registers on  RTP is HIGH, the tangular conversion
ENYP <sub>1,0</sub>	when ENXR is HIGH. When ENXR is  The value presented to the YPIN the current clock, as determined  ENYP1,0 INST  00 No 10 M re 10 C re 11 M re	input port is less to be current transport output ports.	e stored in to latched into linputs ENYF ed, current enabled, C da enabled, M da O, C registe odulation re sformation m ion. When R	the phase accumulator ing P1,0 as shown below:  data held ata held ata held er input  gister, and 0=LOW, 1=HIGH node of the device. When	out registers on  RTP is HIGH, the tangular conversion
ENXR ENYP1,0	when ENXR is HIGH. When ENXR is  The value presented to the YPIN the current clock, as determined  ENYP1,0 INST  00 No 10 M re 10 C re 11 M re	input port is liby the control  TRUCTION  registers enable egister input e egister input e egister set to bled  and M is the Mone current transpropries convers and output ports tatic input.	e stored in to latched into linputs ENYF ed, current enabled, C da enabled, M da O, C registe odulation re sformation m ion. When R	the phase accumulator ing P1,0 as shown below:  data held ata held ata held er input  gister, and 0=LOW, 1=HIGH node of the device. When	out registers on  RTP is HIGH, the tangular conversion

## TABLE III. PIN FUNCTIONS (cont.) ACC<sub>1,0</sub> In applications utilizing the device to perform waveform synthesis and modulation in the Polar-To-Rectangular mode (RTP=LOW), the user determines the internal phase Accumulator structure implemented on the next clock by setting the accumulator control word $\mbox{ACC}_{1,0}$ , as shown below: ACC<sub>1,0</sub> CONFIGURATION <u>00</u> No accumulation performed 01 PM accumulator path enabled 10 FM accumulator path enabled 11 (Nonsensical) logical OR of PM and FM where 0=LOW, 1=HIGH. The accumulator will roll over correctly when full scale is exceeded, allowing the user to perform continuous phase accumulation through $2\pi$ radians, or 360 degrees. Note that the accumulators will also function when RTP = HIGH (Retangular-To-Polar), which is useful when performing backward mapping from Cartesian to polar coordinates; however, most applications will require that ${\tt ACC}_{1,0}$ be set to 00 to avoid accumulating the Cartesian Y input data. TCXY The format select control sets the numeric format of the Rectangular data, whether input (RTP=HIGH) or output (RTP=LOW). This control indicates two's complement format when TCXY=HIGH, and sign-andmagnitude when LOW. This is a static input. OVF When RTP=LOW (Polar-To-Rectangular), the Overflow Flag will go WIGH on the clock that the magnitude of either of the current Cartesian coordinate outputs exceeds the maximum range. It will return LOW on the clock that the Cartesian out-put values(s) return to full-scale or less. OERX, OEPY Data in the output registers are available at the outputs of the device when the respective asynchronous Output Enables are LOW. When OERX or OEPY is HIGH, the respective output port(s) is in the high-impedance state. **STANDARDIZED** SIZE 5962-92331 MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444 REVISION LEVEL SHEET

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6.6 One part - one part number system. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the three major microcircuit requirement, documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document <u>listing</u>
New MIL-H-38534 Standardized Military Drawings	5962-XXXXXZZ(H or K)YY	QML - 38534	MIL-BUL-103
New MIL-I-38535 Standardized Military Drawings	5962-XXXXXZZ(Q or V)YY	QML -38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standardized Military Drawings	5962-XXXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

#### 6.7 Sources of supply.

- 6.7.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.
- 6.7.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

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